L Numb r	Hits	S arch T xt	DB	Time stamp
1	2	("6387734").PN.	USPAT;	2002/07/22
			US-PGPUB;	13:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	2	("6350668").PN.	USPAT;	2002/07/22
			US-PGPUB;	13:31
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	2	("6350633").PN.	USPAT;	2002/07/22
İ			US-PGPUB;	13:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	3	("6329288").PN.	USPAT;	2002/07/22
			US-PGPUB;	13:34
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	42	(US-6271056-\$ or US-6153448-\$ or	USPAT;	2002/07/22
		US-6020629-\$ or US-5977641-\$ or	US-PGPUB	13:39
		US-6350668-\$ or US-6075290-\$ or		
		US-6130480-\$ or US-6278192-\$ or		
		US-6326701-\$ or US-5949142-\$ or		
		US-5886415-\$ or US-5889333-\$ or		
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
İ		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
		US-6380574-\$ or US-6297544-\$ or		
1		US-6403460-\$ or US-6181569-\$).did. or		
ļ		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20020064935-\$ or		
		US-20020001937-\$ or		
		US-20020076911-\$).did.		
6	0	("I5 and ((copper or silver) near paste)").PN.	USPAT;	2002/07/22
			US-PGPUB;	13:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	1 -	//IIC COTACEC & IIC CATCALLO &	1.00.00	0000/05/55
7	1	((US-6271056-\$ r US-6153448-\$ r	USPAT;	2002/07/22
		US-6020629-\$ r US-5977641-\$ or	US-PGPUB;	13:42
		US-6350668-\$ r US-6075290-\$ r	EPO; JPO;	
		US-6130480-\$ or US-6278192-\$ r	DERWENT;	
		US-6326701-\$ r US-5949142-\$ r	IBM_TDB	
		US-5886415-\$ or US-5889333-\$ or		
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
	1	US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
		US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20020064935-\$ or		
		US-20020001937-\$ or		
		US-20020076911-\$).did.) and ((copper or		
		silver) near paste)		
8	2	((US-6271056-\$ or US-6153448-\$ or	USPAT;	2002/07/22
		US-6020629-\$ or US-5977641-\$ or	US-PGPUB;	13:48
		US-6350668-\$ or US-6075290-\$ or	EPO; JPO;	
		US-6130480-\$ or US-6278192-\$ or	DERWENT;	
		US-6326701-\$ or US-5949142-\$ or	IBM_TDB	
		US-5886415-\$ or US-5889333-\$ or		
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
		US-6380574-\$ or US-6297544-\$ or		
	-	US-6403460-\$ or US-6181569-\$).did. or		
		(US-6350633-\$ or US-6107164-\$).did. or		
	1	(US-20020056741-\$ or US-20020094601-\$ or		
	I	US-20020005568-\$ or US-20020033530-\$ or		
		02-20020003300-3 01 03-20020033330-3 01		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or US-20010040285-\$ or US-20010008304-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or US-20010040285-\$ or US-20010008304-\$ or US-20010002064-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or US-20010040285-\$ or US-20010008304-\$ or US-20010002724-\$ or US-20010002064-\$ or US-20010002069-\$ or US-20020064935-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or US-20010040285-\$ or US-20010008304-\$ or US-20010002724-\$ or US-20010002064-\$ or US-20010002069-\$ or US-20020064935-\$ or US-20020001937-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or US-20010040285-\$ or US-20010008304-\$ or US-20010002724-\$ or US-20010002064-\$ or US-20010002069-\$ or US-20020064935-\$ or		

9	4	((US-6271056-\$ or US-6153448-\$ r	USPAT;	2002/07/22
•		US-6020629-\$ or US-5977641-\$ or	US-PGPUB;	13:49
		US-6350668-\$ r US-6075290-\$ r	EPO; JPO;	
		US-6130480-\$ or US-6278192-\$ or	DERWENT:	
		US-6326701-\$ r US-5949142-\$ r	IBM_TDB	
		US-5886415-\$ or US-5889333-\$ or	10	
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or	1	
		US-6380574-\$ or US-6297544-\$ or		
			4	
		US-6403460-\$ or US-6181569-\$).did. or (US-6350633-\$ or US-6107164-\$).did. or	į.	
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-2002005568-\$ or US-20020033530-\$ or		
		US-2002005966-\$ or US-20020033536-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002724-\$ or US-20020064935-\$ or		
		US-20020001937-\$ or		
		US-20020076911-\$).did.) and ((conductive or		
		conducting) near (resin or epoxy))		
10	11	((US-6271056-\$ or US-6153448-\$ or	USPAT;	2002/07/22
10	· ' '	US-6020629-\$ or US-5977641-\$ or	US-PGPUB;	13:51
		US-6350668-\$ or US-6075290-\$ or	EPO; JPO;	10.01
		US-6130480-\$ or US-6278192-\$ or	DERWENT;	
		US-6326701-\$ or US-5949142-\$ or	IBM TDB	
		US-5886415-\$ or US-5889333-\$ or	15111_155	
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
	1	US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20020064935-\$ or		
		U3-ZUUZUUU1937-3 Or		
		US-20020001937-\$ or US-20020076911-\$).did.) and ((conductive or		
		US-20020001937-3 or US-20020076911-\$).did.) and ((conductive or conducting) near5 (resin or epoxy))		

11	14	((US-6271056-\$ r US-6153448-\$ r	USPAT;	2002/07/22
		US-6020629-\$ or US-5977641-\$ or	US-PGPUB;	13:51
	·	US-6350668-\$ or US-6075290-\$ or	EPO; JPO;	
		US-6130480-\$ r US-6278192-\$ or	DERWENT;	
		US-6326701-\$ or US-5949142-\$ or	IBM_TDB	
		US-5886415-\$ r US-5889333-\$ or		
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
		US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
•		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20020064935-\$ or		
		US-20020001937-\$ or		
		US-20020076911-\$).did.) and ((conductive or		
		conducting) near5 (resin or epoxy or paste))		
12	16	((US-6271056-\$ or US-6153448-\$ or	USPAT;	2002/07/22
		US-6020629-\$ or US-5977641-\$ or	US-PGPUB;	14:07
		US-6350668-\$ or US-6075290-\$ or	EPO; JPO;	
		US-6130480-\$ or US-6278192-\$ or	DERWENT;	
		US-6326701-\$ or US-5949142-\$ or	IBM_TDB	
		US-5886415-\$ or US-5889333-\$ or		
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		,
		US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002724-\$ or US-20010002004-\$ or US-20010002069-\$ or		
		US-20020001937-\$ or		
		US-20020001937-5 or US-20020076911-\$).did.) and ((conductive or		
		• • •		
	I	conducting) near5 (resin or epoxy or paste	1	
		or solder))	1	

13	4	(((US-6271056-\$ r US-6153448-\$ or	USPAT;	2002/07/22
		US-6020629-\$ r US-5977641-\$ or	US-PGPUB;	14:09
		US-6350668-\$ r US-6075290-\$ or	EPO; JPO;	
		US-6130480-\$ r US-6278192-\$ or	DERWENT:	
		US-6326701-\$ r US-5949142-\$ or	IBM TDB	
		US-5886415-\$ r US-5889333-\$ or	_	
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
		US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
	-	(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-2002005568-\$ or US-20020033530-\$ or		
		US-20020005366-5 or US-20020033530-5 or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010040283-\$ or US-2001000330-\$ or US-20010002064-\$ or		
		US-20010002724-\$ or US-20010002004-\$ or US-20010002069-\$ or		
		US-20020001937-\$ or		
		US-20020001937-5 of US-20020076911-\$).did.) and ((conductive or		
		conducting) near5 (resin or epoxy or paste		
		or solder))) and (solder near resist)		
14	. 5	(((US-6271056-\$ or US-6153448-\$ or	USPAT;	2002/07/22
14	j. 3	US-6020629-\$ or US-5977641-\$ or	US-PGPUB;	14:09
		US-6350668-\$ or US-6075290-\$ or	EPO; JPO;	14.03
		US-6130480-\$ or US-6278192-\$ or	DERWENT;	
		US-6326701-\$ or US-5949142-\$ or	IBM_TDB	
		US-5886415-\$ or US-5889333-\$ or	IBM_IBB	
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		:
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020005966-\$ or US-20020033530-\$ or US-20020034872-\$ or		
		•		
		US-20010040285-\$ or US-20010008304-\$ or		
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20020064935-\$ or		
		US-20020001937-\$ or		
		US-20020076911-\$).did.) and ((conductive or		
	1	conducting) near5 (resin or epoxy or paste		
	1	or solder))) and (solder near5 resist)		

15	7	(((US-6271056-\$ or US-6153448-\$ or	USPAT;	2002/07/22
		US-6020629-\$ or US-5977641-\$ r	US-PGPUB;	14:09
		US-6350668-\$ or US-6075290-\$ r	EPO; JPO;	
		US-6130480-\$ or US-6278192-\$ r	DERWENT;	
		US-6326701-\$ or US-5949142-\$ or	IBM_TDB	
			IBM_IDB	
		US-5886415-\$ r US-5889333-\$ r		
		US-5892273-\$ or US-6355975-\$ or		
		US-6365439-\$ or US-6355500-\$ or		
		US-6342728-\$ or US-6307269-\$ or		
		US-6353255-\$ or US-6342726-\$ or		
		US-6329288-\$ or US-6387734-\$ or		
		US-6380574-\$ or US-6297544-\$ or		
		US-6403460-\$ or US-6181569-\$).did. or		
		(US-6350633-\$ or US-6107164-\$).did. or		
		(US-20020056741-\$ or US-20020094601-\$ or		
		US-20020005568-\$ or US-20020033530-\$ or		
		US-20020050642-\$ or US-20020034872-\$ or		
		US-20010040285-\$ or US-20010008304-\$ or	1	
		US-20010002724-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20020064935-\$ or		
		US-20020001937-\$ or		
		US-20020076911-\$).did.) and ((conductive or		
		conducting) near5 (resin or epoxy or paste		
		or solder))) and (photosensitive)		
	1	crack and warp and (csp or "chip scale	USPAT;	2002/07/19
•	•		US-PGPUB;	11:30
		package") and "wafer level"	·	11:30
			EPO; JPO; DERWENT;	
			· ·	
	_		IBM_TDB	2002/07/40
•	7	crack and warp and (csp or "chip scale	USPAT;	2002/07/19
		package") and wafer	US-PGPUB;	11:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8	, , ,	USPAT	2002/07/19
		"5949142"   "6051450"   "6075290"		11:31
		"6111309"   "6130480").PN.		
-	424	tsubosaki	USPAT;	2002/07/19
			US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	256	tsubosaki and kunihiro	USPAT;	2002/07/19
			US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	o	kunihiro adj tsubosaki	USPAT;	2002/07/19
-		nammio auj tauboaani	US-PGPUB;	11:33
				11133
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

ſ.	256	kunihir neartsubosaki	USPAT;	2002/07/19
-	233	Name ileai tsavosani	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	kunihir adj2 tsubosaki	USPAT;	2002/07/19
_		Railini daja toaboodki	US-PGPUB;	11:33
	-		EPO; JPO;	
			DERWENT;	
:	]		IBM_TDB	
_	O	kunihiro adj10 tsubosaki	USPAT;	2002/07/19
			US-PGPUB;	11:33
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	24	(kunihiro near tsubosaki) and csp	USPAT;	2002/07/19
	] ,		US-PGPUB;	11:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	temperature and crack and warp and	USPAT;	2002/07/19
		substrate and yield and ((polish or polished	US-PGPUB;	11:38
		or polishing) near (insulation or isolation or	EPO; JPO;	
		insulating or dielectric))	DERWENT;	
			IBM_TDB	
-	1075	(polish or polishing or polished) near	USPAT;	2002/07/19
		(insulating or isolation or insulation or	US-PGPUB;	11:39
		dielectric)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((polish or polishing or polished) near	USPAT;	2002/07/19
	<u> </u>	(insulating or isolation or insulation or	US-PGPUB;	11:39
		dielectric)) and electroles	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	24	((polish or polishing or polished) near	USPAT;	2002/07/19
	:	(insulating or isolation or insulation or	US-PGPUB;	11:40
		dielectric)) and electroless	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/27/46
•	1	(((polish or polishing or polished) near	USPAT;	2002/07/19
		(insulating or isolation or insulation or	US-PGPUB;	11:41
		dielectric)) and electroless) and csp	EPO; JPO;	
	]		DERWENT;	
			IBM_TDB	0000/07/40
•	0	(((polish or polishing or polished) near	USPAT;	2002/07/19
		(insulating or isolation or insulation or	US-PGPUB;	11:41
		dielectric)) and electroless) and ("chip scale	EPO; JPO;	
		package")	DERWENT;	
	1		IBM_TDB	

	191647	I ctrode near10 (insulati n or insulating r	USPAT;	2002/07/19
	13104	isolation or dielectric)	US-PGPUB;	11:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	20447	I ctrod n ar (insulati n r insulating r	USPAT;	2002/07/19
•	20447	_	US-PGPUB;	11:44
	}	isolation or dielectric)	EPO; JPO;	11:44
			DERWENT;	
			IBM_TDB	
	63	(electrode near (insulation or insulating or	USPAT;	2002/07/19
<del>-</del>	03	isolation or dielectric)) and electroless and	1	11:44
		· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	11:44
		(polish or polishing or polished)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/07/40
•	1	((electrode near (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric)) and electroless and	US-PGPUB;	11:44
		(polish or polishing or polished)) and csp	EPO; JPO;	
	-		DERWENT;	
			IBM_TDB	2222/27/42
-	144602	electrode near5 (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric)	US-PGPUB;	11:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	259	(electrode near5 (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric)) and electroless and	US-PGPUB;	11:44
		(polish or polishing or polished)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	((electrode near5 (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric)) and electroless and	US-PGPUB;	11:46
		(polish or polishing or polished)) and csp	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	0	((electrode near5 (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric)) and electroless and	US-PGPUB;	11:46
		(polish or polishing or polished)) and	EPO; JPO;	
		kunihiro and tsubosaki	DERWENT;	
			IBM_TDB	
•	7	(electrode near5 (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric)) and kunihiro and	US-PGPUB;	11:47
		tsubosaki	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	24	csp and kunihiro and tsubosaki	USPAT;	2002/07/19
			US-PGPUB;	11:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	1		<del></del>	
-	0	(("electr lytic plate" or "electr lytic plat d")	USPAT;	2002/07/19
		and csp) and el ctr l ss	US-PGPUB;	11:52
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
-	5	("electr lytic plat " or "el ctrolytic plat d")	USPAT;	2002/07/19
		and csp	US-PGPUB;	11:52
	;		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	123	("electrolytic plate" or "electrolytic plated")	USPAT;	2002/07/19
		and electroless	US-PGPUB;	11:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	o	(("electrolytic plate" or "electrolytic plated")	USPAT;	2002/07/19
		and electroless) and tsubosaki and kunihiro	US-PGPUB;	11:53
		and discussions, and tous sound and naming	EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
_	64	electrolytic and electroless and csp	USPAT;	2002/07/19
}	04	electionytic and electroless and csp	US-PGPUB;	11:54
			·	11.54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/07/40
-	64	(electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp	US-PGPUB;	11:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/0=/40
-	0	((electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp) and tsubosaki	US-PGPUB;	11:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	16	((electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp) and crack	US-PGPUB;	11:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	(((electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp) and crack) and warp	US-PGPUB;	11:56
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp) and (csp.ti.)	US-PGPUB;	11:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	1	((electrolytic or el ctr lytically) and	USPAT;	2002/07/19
		el ctroless and csp) and (csp.clm.)	US-PGPUB;	11:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	30	((electrolytic or el ctrolytically) and	USPAT;	2002/07/19
		electroless and csp) and csp and wafer	US-PGPUB;	11:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	29	(((electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp) and csp and wafer) and	US-PGPUB;	11:58
		(bump or solder or ball)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	((((electrolytic or electrolytically) and	USPAT;	2002/07/19
		electroless and csp) and csp and wafer) and	US-PGPUB;	12:01
		(bump or solder or ball)) and (polish or	EPO; JPO;	
		polished or polishing)	DERWENT;	
		, ponence et ponenn <b>g</b> ,	IBM_TDB	
-	134	(csp or "chip size package" or "chip scale	USPAT;	2002/07/19
		package") and (plate or plated or plating)	US-PGPUB;	12:03
		and (polish or polished or polishing) and	EPO; JPO;	12.00
		wafer	DERWENT;	
			IBM_TDB	
l <u>-</u>	o	(((csp or "chip size package" or "chip scale	USPAT;	2002/07/19
		package") and (plate or plated or plating)	US-PGPUB;	12:05
		and (polish or polished or polishing) and	EPO; JPO;	12.03
]		wafer) and (electrolytic or electrolytically)	DERWENT;	
		* * * * * * * * * * * * * * * * * * * *		
	30	and electroless) and tsubosaki	IBM_TDB	2002/07/19
-	30	((csp or "chip size package" or "chip scale	USPAT;	12:07
		package") and (plate or plated or plating)	US-PGPUB;	12:01
	i	and (polish or polished or polishing) and	EPO; JPO;	
		wafer) and (electrolytic or electrolytically)	DERWENT;	
		and electroless	IBM_TDB	0000/07/40
-	36	(US-6326701-\$ or US-6278192-\$ or	USPAT;	2002/07/19
1		US-6130480-\$ or US-6075290-\$ or	US-PGPUB	12:11
		US-5949142-\$ or US-5892273-\$ or		
		US-5889333-\$ or US-5886415-\$ or		
		US-6365439-\$ or US-6355975-\$ or		
		US-6355500-\$ or US-6353255-\$ or		
		US-6342728-\$ or US-6342726-\$ or		
		US-6307269-\$ or US-6329288-\$ or		
		US-6387734-\$ or US-6380574-\$ or		
		US-6297544-\$ or US-6350633-\$ or		
		US-6181569-\$ or US-6107164-\$ or		
		US-6350668-\$ or US-6153448-\$ or		
		US-5977641-\$).did. or (US-20020034872-\$ or		
	[	US-20020050642-\$ r US-20010040285-\$ or		
		US-20010008304-\$ r US-20010002064-\$ or		
		US-20010002069-\$ r US-20010002724-\$ r		
]		US-20020033530-\$ r US-20020001937-\$ r		
		US-20020076911-\$ r		
1	1	US-20020064935-\$).did.		

•	9	((US-6326701-\$ r US-6278192-\$ r	USPAT;	2002/07/19
		US-6130480-\$ r US-6075290-\$ r	US-PGPUB;	12:19
		US-5949142-\$ r US-5892273-\$ or	EPO; JPO;	
		US-5889333-\$ r US-5886415-\$ r	DERWENT;	
		US-6365439-\$ r US-6355975-\$ or	IBM_TDB	
		US-6355500-\$ r US-6353255-\$ or		
		US-6342728-\$ or US-6342726-\$ or		
		US-6307269-\$ or US-6329288-\$ or		
		US-6387734-\$ or US-6380574-\$ or		
		US-6297544-\$ or US-6350633-\$ or		
		US-6181569-\$ or US-6107164-\$ or		
		US-6350668-\$ or US-6153448-\$ or		
		US-5977641-\$).did. or (US-20020034872-\$ or		
		US-20020050642-\$ or US-20010040285-\$ or		
		US-20010008304-\$ or US-20010002064-\$ or		
		US-20010002069-\$ or US-20010002724-\$ or	•	
		US-20020033530-\$ or US-20020001937-\$ or		
		US-20020076911-\$ or		
		US-20020064935-\$).did.) and wafer and		
		(polish or polished or polishing) and		
		(isolation or insulating or dielectric or		
		passivation) and electroless and (plating or		
		plate or plated) and (electrolytic or		
		electrolytically) and (etch or etched or		
		etching) and (bump or solder or ball)		
-	111	wafer and (polish or polished or polishing)	USPAT;	2002/07/19
;		and (isolation or insulating or dielectric or	US-PGPUB;	12:15
		passivation) and electroless and (plating or	EPO; JPO;	
		plate or plated) and (electrolytic or	DERWENT;	
		electrolytically) and (etch or etched or	IBM_TDB	
		etching) and (bump or solder or ball)	_	
•	o	((wafer and (polish or polished or polishing)	USPAT;	2002/07/19
		and (isolation or insulating or dielectric or	US-PGPUB;	12:16
		passivation) and electroless and (plating or	EPO; JPO;	
		plate or plated) and (electrolytic or	DERWENT;	
		electrolytically) and (etch or etched or	IBM_TDB	
	:	etching) and (bump or solder or ball) ) and	_	
		(csp or "chip scale package" or "chip size		
		package")) and tsubosaki		
•	29	(wafer and (polish or polished or polishing)	USPAT;	2002/07/19
		and (isolation or insulating or dielectric or	US-PGPUB;	12:17
		passivation) and electroless and (plating or	EPO; JPO;	
		plate or plated) and (electrolytic or	DERWENT;	
	•	electrolytically) and (etch or etched or	IBM_TDB	
		etching) and (bump or solder or ball) ) and		
		(csp or "chip scale package" or "chip size		
		package")		

•	15	wafer and (polish rp lish d rp lishing) and (is lati n rinsulating rdi lectric r	USPAT; US-PGPUB;	2002/07/19 12:20
		passivati n) and I ctroless and (plating r plat r plated) and (electrolytic r	EPO; JPO; DERWENT;	
		I ctrolytically) and (etch r tched r tching) and (bump or s Ider or ball) and	IBM_TDB	
		(csp or "chip scale package" or "chip size		
_	4	package") and (cure or curing or cured) wafer and (polish or polished or polishing)	USPAT;	2002/07/19
		and (isolation or insulating or dielectric or	US-PGPUB;	12:21
		passivation) and electroless and (plating or plate or plated) and (electrolytic or	EPO; JPO; DERWENT;	
		electrolytically) and (etch or etched or	IBM_TDB	
		etching) and (bump or solder or ball) and (csp or "chip scale package" or "chip size		
		package") and (cure or curing or cured) and		
	2	((conductive or conducting) near10 paste) wafer and (polish or polished or polishing)	USPAT;	2002/07/19
•		and (isolation or insulating or dielectric or	US-PGPUB;	12:34
		passivation) and electroless and (plating or	EPO; JPO; DERWENT;	
		plate or plated) and (electrolytic or electrolytically) and (etch or etched or	IBM_TDB	
		etching) and (bump or solder or ball) and (csp or "chip scale package" or "chip size		
		package") and (cure or curing or cured) and		
		((conductive or conducting) near10 paste) and (sputter or sputtering or sputtered)		
-	1	((polishing near (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric or passivation)) and (electroless adj (plate or plated or plating))	US-PGPUB; EPO; JPO;	12:38
		and ((electrolytic or electrolytically) adj	DERWENT;	
		(plate or plated or plating)) and (etch or etching or etched))	IBM_TDB	
-	1	((polishing near (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric or passivation)) and (electroless near (plate or plated or plating))	US-PGPUB; EPO; JPO;	12:39
		and ((electrolytic or electrolytically) near	DERWENT;	
		(plate or plated or plating)) and (etch or etching or etched))	IBM_TDB	
-	5864	(polishing near (insulation or insulating or	USPAT;	2002/07/19
		isolation or dielectric or passivation)) electroless and electrolytic	US-PGPUB; EPO; JPO;	12:40
			DERWENT;	
	5	(polishing near (insulation or insulating or	IBM_TDB USPAT;	2002/07/19
		isolation or dielectric or passivation)) and	US-PGPUB;	12:41
		electroless and electrolytic	EPO; JPO; DERWENT;	
			IBM_TDB	
•	41	(p lishing n ar5 (insulati n r insulating or is lati n or diel ctric r passivati n)) and	USPAT; US-PGPUB;	2002/07/19 12:42
		electrol ss and el ctrolytic	EPO; JPO;	
			DERWENT; IBM_TDB	
	<u> </u>			<u></u>

	1	((p lishing near5 (insulati n r insulating or	USPAT;	2002/07/19
-	•	is lati n or di l ctric r passivati n)) and	US-P PUB;	12:44
		el ctr less and electr lytic) and csp	EPO; JPO;	12.77
		er ctr less and electr lytic, and csp	DERWENT;	
			-	
	40000	/inculation on inculation and it assis as	IBM_TDB	2002/07/40
•	10809	(insulation or insulating or di 1 ctric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:44
		polishing)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	90	((insulation or insulating or dielectric or	USPAT;	2002/07/19
	1	isolation) near10 (polish or polished or	US-PGPUB;	12:44
		polishing)) and electroless and electrolytic	EPO; JPO;	
	Ì		DERWENT;	
			IBM_TDB	
-	68	(((insulation or insulating or dielectric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:45
		polishing)) and electroless and electrolytic)	EPO; JPO;	
		and (sputter or sputtering or sputtered)	DERWENT;	
			IBM_TDB	
-	67	((((insulation or insulating or dielectric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:48
		polishing)) and electroless and electrolytic)	EPO; JPO;	
		and (sputter or sputtering or sputtered)) and	DERWENT;	
		(etch or etched or etching)	IBM_TDB	
-	41	(((((insulation or insulating or dielectric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:45
		polishing)) and electroless and electrolytic)	EPO; JPO;	
		and (sputter or sputtering or sputtered)) and	DERWENT;	
		(etch or etched or etching)) and wafer	IBM_TDB	
-	2	((((((insulation or insulating or dielectric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:47
		polishing)) and electroless and electrolytic)	EPO; JPO;	
		and (sputter or sputtering or sputtered)) and	DERWENT;	
		(etch or etched or etching)) and wafer) and	IBM_TDB	
		csp	_	
	1	((((((insulation or insulating or dielectric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:47
		polishing)) and electroless and electrolytic)	EPO; JPO;	
		and (sputter or sputtering or sputtered)) and	DERWENT;	
		(etch or etched or etching)) and wafer) and	IBM_TDB	
		("chip size" or "chip scale")	_	
•	3895	(((((insulation or insulating or dielectric or	USPAT;	2002/07/19
		isolation) near10 (polish or polished or	US-PGPUB;	12:48
		polishing)) and electroless and electrolytic)	EPO; JPO;	
		and (sputter or sputtering or sputtered)) and	DERWENT;	
	1	(etch or etched or etching)) csp	IBM_TDB	
•	2	(((((insulation or insulating or dielectric or	USPAT;	2002/07/19
		is lati n) n ar10 (p lish or polish d r	US-P PUB;	12:48
		p lishing)) and electroless and   ctrolytic)	EPO; JPO;	<del></del>
		and (sputter r sputtering or sputt r d)) and	DERWENT;	
		(etch retch dor tching)) and csp	IBM_TDB	

-	110	el ctr de and (insulation or insulating r	USPAT;	2002/07/19
		diel ctric r passivation) and (wiring or	US-PGPUB;	12:52
		metal rint rc nnect rwir r	EP ; JPO;	
		interc nn cti n) and bump and paste and	DERWENT;	
		(cur r cure r curing) and (c nductive r	IBM_TDB	
		c nducting rc nduct) and s ld rand		
		resist		
-	76	electrode and (insulation or insulating or	USPAT;	2002/07/19
		dielectric or passivation) and (wiring or	US-PGPUB;	12:53
		metal or interconnect or wire or	EPO; JPO;	
		interconnection) and bump and paste and	DERWENT;	
		(cure or cure or curing) and (conductive or	IBM_TDB	
		conducting or conduct) and solder and	_	
		resist and ball and (plate or plating or		
		plated)		
_	63	electrode and (insulation or insulating or	USPAT;	2002/07/19
	55	dielectric or passivation) and (wiring or	US-PGPUB;	12:53
		metal or interconnect or wire or	EPO; JPO;	12.00
		interconnection) and bump and paste and	DERWENT;	
	,	(cure or cure or curing) and (conductive or	IBM TDB	
		-, ,	IDIAI I DD	
		conducting or conduct) and solder and		
		resist and ball and (plate or plating or		
		plated) and (etch or etched or etching)		0000/07/40
•	33	electrode and (insulation or insulating or	USPAT;	2002/07/19
		dielectric or passivation) and (wiring or	US-PGPUB;	12:54
		metal or interconnect or wire or	EPO; JPO;	
		interconnection) and bump and paste and	DERWENT;	
		(cure or cure or curing) and (conductive or	IBM_TDB	
		conducting or conduct) and solder and		
		resist and ball and (plate or plating or		
		plated) and (etch or etched or etching) and		
		(sputter or sputtering or sputtered)		
-	24	electrode and (insulation or insulating or	USPAT;	2002/07/19
		dielectric or passivation) and (wiring or	US-PGPUB;	12:54
		metal or interconnect or wire or	EPO; JPO;	
		interconnection) and bump and paste and	DERWENT;	
		(cure or cure or curing) and (conductive or	IBM_TDB	
	i e	conducting or conduct) and solder and		
		resist and ball and (plate or plating or		
		plated) and (etch or etched or etching) and		
		(sputter or sputtering or sputtered) and		
		wafer		
•	6	electrode and (insulation or insulating or	USPAT;	2002/07/19
		dielectric or passivation) and (wiring or	US-PGPUB;	12:58
		metal or interconnect or wire or	EPO; JPO;	
		interconnection) and bump and paste and	DERWENT:	
		(cure or cure or curing) and (conductive or	IBM_TDB	
		conducting or conduct) and solder and	10111_100	
		r sist and ball and (plate r plating r		
		,- · · · · · · · · · · · · · · · · · · ·		
		plated) and (etch or etched retching) and		}
		(sputter r sputtering or sputtered) and		
	l	wafer and csp	1	

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-	17	(((csp r "chip scal package" or "chip siz	USPAT;	2002/07/19
		package").clm.) and wafer) and lectr less	US-PGPUB;	13:27
		and I ctrolytic	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/07/40
-	69	(((csp r"chip scale package" r"chip siz	USPAT;	2002/07/19
		package") and wafer).clm.) and wafer	US-PGPUB;	13:41
			EPO; JPO;	
	1		DERWENT; IBM_TDB	
_	19	(((csp or "chip scale package" or "chip size	USPAT:	2002/07/19
•	19	package") and wafer).clm.) and wafer and	US-PGPUB;	13:38
		((csp or "chip scale package" or "chip size	EPO; JPO;	.0.00
		package").ti.)	DERWENT;	
		puokugo /itii)	IBM_TDB	
_	7	((((csp or "chip scale package" or "chip size	USPAT;	2002/07/19
		package") and wafer).clm.) and wafer and	US-PGPUB;	13:40
		((csp or "chip scale package" or "chip size	EPO; JPO;	
		package").ti.)) and (polish or polished or	DERWENT;	
		polishing)	IBM_TDB	
•	0	(((((csp or "chip scale package" or "chip	USPAT;	2002/07/19
		size package") and wafer).clm.) and wafer	US-PGPUB;	13:39
		and ((csp or "chip scale package" or "chip	EPO; JPO;	
		size package").ti.)) and (polish or polished or	DERWENT;	
		polishing)) and electroless) and electolytic	IBM_TDB	0000/07/40
-	3	(((((csp or "chip scale package" or "chip size	USPAT;	2002/07/19
		package") and wafer).clm.) and wafer and	US-PGPUB;	13:39
•		((csp or "chip scale package" or "chip size	EPO; JPO; DERWENT;	
		package").ti.)) and (polish or polished or polishing)) and electroless	IBM_TDB	
_	5	((((csp or "chip scale package" or "chip size	USPAT;	2002/07/19
	3	package") and wafer).clm.) and wafer and	US-PGPUB:	13:40
		((csp or "chip scale package" or "chip size	EPO; JPO;	
		package").ti.)) and (polish or polished or	DERWENT;	
		polishing) and plating	IBM_TDB	
-	5	((((((csp or "chip scale package" or "chip	USPAT;	2002/07/19
		size package") and wafer).clm.) and wafer)	US-PGPUB;	13:42
		and (polish or polished or polishing) and	EPO; JPO;	
		(plate or plating or plated)) and (etch or	DERWENT;	
		etched or etching)) and (sputter or	IBM_TDB	
		sputtering or sputtered)		0000/07/45
-	7	(((((csp or "chip scale package" or "chip size	USPAT;	2002/07/19
		package") and wafer).clm.) and wafer) and	US-PGPUB;	13:43
		(polish or polished or polishing) and (plate or	EPO; JPO; DERWENT;	
		plating or plated)) and (etch or etched or etching)	IBM_TDB	
_	11	etcning) ((((csp or "chip scale package" or "chip size	USPAT;	2002/07/19
_		package") and wafer).clm.) and wafer) and	US-PGPUB;	13:45
		(p lish rp lish d rp lishing) and (plate r	EPO; JPO;	
		plating r plated)	DERWENT;	
			IBM_TDB	

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•	0	(202/0056741).CCLS.	USPAT; US-PGPUB;	13:45
				13:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/07/40
-	0	(2002/0056741).CCLS.	USPAT;	2002/07/19
			US-PGPUB;	13:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(2002/0056741 A1).CCLS.	USPAT;	2002/07/19
			US-PGPUB;	13:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(US 2002/0056741 A1).CCLS.	USPAT;	2002/07/19
			US-PGPUB;	13:46
			EPO; JPO;	
	ļ		DERWENT;	
			IBM_TDB	
-	28	"0056741"	USPAT;	2002/07/19
			US-PGPUB;	13:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	o	2002/0056741	USPAT;	2002/07/19
			US-PGPUB;	13:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1	09/834,629	USPAT;	2002/07/19
		-	US-PGPUB;	13:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	o	09794,108	USPAT;	2002/07/19
			US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	09/794,108	USPAT;	2002/07/19
		•	US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	09/738,667	USPAT;	2002/07/19
		,	US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	1	("6403460").PN.	USPAT;	2002/07/19
	•	( 0403400 ).FN.		13:49
	-		US-P PUB;	13:49
			EPO; JPO;	
1			DERWENT;	
		(UEOTTC 441) PM	IBM_TDB	0000000000
<b>-</b>	2	("5977641").PN.	USPAT;	2002/07/19
			US-PGPUB;	13:49
			EPO; JPO;	6
			DERWENT;	
	_		IBM_TDB	
-	2	("6350633").PN.	USPAT;	2002/07/19
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("6387734").PN.	USPAT;	2002/07/19
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	10/052,143	USPAT;	2002/07/19
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	3	("6,329,288").PN.	USPAT;	2002/07/19
		( 0,023,200 ) 11.	US-PGPUB;	13:50
			EPO; JPO;	13.30
			DERWENT;	
			1	
	2	///C 250 CC0/// DN	IBM_TDB	0000/07/40
-	2	("6,350,668").PN.	USPAT;	2002/07/19
			US-PGPUB;	13:51
			EPO; JPO;	
			DERWENT;	
		(10 404 T001) TV	IBM_TDB	
•	2	("6,181,569").PN.	USPAT;	2002/07/19
			US-PGPUB;	13:51
	]		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	0	("97 98 99 100 101 102 103 04 105 106 107	USPAT;	2002/07/19
		108").PN.	US-PGPUB;	13:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	440	09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:52
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		tsub saki 10/052,143 (("6,329,288").PN.)	DERWENT;	
		(("6,350,668").PN.) (("6,181,569").PN.)	IBM_TDB	
	<del></del>	" ->> /:: III		

	18	09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:52
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)	_	
-	8	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:53
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode	12	
_	8	((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:54
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode) and		
		(wiring or metal or interconnect or		
		interconnection or wire)		
_	5	(((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:54
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
į		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode) and	15155	
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump		
_	5	((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
	J	09/738,667 (("6403460").PN.)	US-PGPUB;	13:55
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	13.33
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode) and	15111_155	
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder		
_	2	(((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
•	2	09/738,667 (("6403460").PN.)	US-PGPUB;	
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	13:56
		(("6387734").PN.) 10/052,143	, ,	
			DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode) and		
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder) and (cure or cured or curing)		

-	2	((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:56
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and lectr d ) and		
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder) and (cure or cured or curing)) and		
		(plate or plating or plated)		
	2	((((((09/834,629 09794,108 09/794,108	USPAT:	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:56
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode) and	12	
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder) and (cure or cured or curing)) and		
		(plate or plating or plated)) and (polish or		
		polished or polishing or grind or grinding or		
		grinded)		
	2	,	HEDAT.	2002/07/19
		((((((((09/834,629 09794,108 09/794,108	USPAT;	13:57
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:57
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	,
		(("6,181,569").PN.)) and electrode) and		
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder) and (cure or cured or curing)) and		
		(plate or plating or plated)) and (polish or		
		polished or polishing or grind or grinding or		
		grinded)) and (etch or etched or etching)		
	2	(((((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	13:57
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode) and		
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder) and (cure or cured or curing)) and		
		(plate or plating or plated)) and (polish or		
		polished or polishing or grind or grinding or		
		grinded)) and (etch or etched or etching))		
		and (sputter or sputtered or sputtering)	•	

	0	((((((((((((((((((((((((((((((((((((((	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:58
-	124	paste ((polish or polishing or polished) near (insulating or isolation or insulation or dielectric)) and resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:58
	2	((((((((((((((((((((((((((((((((((((((	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:58
•	2	((((((((((((((((((((((((((((((((((((((	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:59

-	0	(((((((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
1		09/738,667 (("6403460").PN.)	US-PGPUB;	14:01
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electr de) and		
		(wiring or metal or interconnect or		
		interconnection or wire)) and bump) and		
		solder) and (cure or cured or curing)) and		
		(plate or plating or plated)) and (polish or		
ļ		polished or polishing or grind or grinding or		
ļ		grinded)) and (etch or etched or etching))		
		and (sputter or sputtered or sputtering)) and		
		(resin or epoxy or paste)) and ((cure or		
		cured or curing) near10 (epoxy or resin or		
		paste) near10 (conducting or conductive or		
		conduct))		
-	8	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:09
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (polishing or	_	
		polished or polish or grinding or grinded or		
		grind) and (plate or plating or plated) and		
		(etch or etched or etching) and (solder or		
		bump or ball) and (sputter or sputtered or		
		sputtering)		
	7	((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
	-	09/738,667 (("6403460").PN.)	US-PGPUB;	14:04
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (polishing or	1811-188	
		1 1 1 1 1 1 1 1 1		
		polished or polish or grinding or grinded or		
		grind) and (plate or plating or plated) and		
		(etch or etched or etching) and (solder or		
ļ		bump or ball) and (sputter or sputtered or		
	_	sputtering) ) and electroless	HODAT	0000/07/40
1 -	7	(((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:04
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
	;	(("6387734").PN.) 10/052,143	DERWENT;	
1		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (polishing or		
		polished or polish or grinding or grinded or		
		grind) and (plate or plating or plated) and		
		(etch or etched or etching) and (solder or		
		bump rball) and (sputt r rsputter d r		
		sputtering)) and el ctr less) and		
	1	el ctr lytic		

4

-	7	((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:06
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT:	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (p lishing r		
		polished or polish or grinding or grinded or		
		grind) and (plate or plating or plated) and		
		(etch or etched or etching) and (solder or		
-		bump or ball) and (sputter or sputtered or		
		sputtering) ) and electroless) and		
		electrolytic) and ("wiring layer" or "wire		
		layer" or "metal layer" or interconnect or		
	-	interconnection)		
	1	((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:07
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (polishing or	15155	
		polished or polish or grinding or grinded or		
		grind) and (plate or plating or plated) and		
		(etch or etched or etching) and (solder or		
		bump or ball) and (sputter or sputtered or		
		sputtering) ) and electroless) and		
		electrolytic) and ("wiring layer" or "wire		
	1	layer" or "metal layer" or interconnect or		
		interconnection)) and ((conductive or		
		conducting or conduct) near10 (paste or		
	_	epoxy or resin))) and (solder near10 resist)	HEDAT.	2002/07/40
-	5	(((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:07
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (polishing or		
		polished or polish or grinding or grinded or		
		grind) and (plate or plating or plated) and		
		(etch or etched or etching) and (solder or		
		bump or ball) and (sputter or sputtered or		
		sputtering) ) and electroless) and		
		electrolytic) and ("wiring layer" or "wire		
		layer" or "metal layer" or interconnect or		
		interconnection)) and ((conductive or		
		conducting or conduct) near10 (paste or		
		epoxy or resin))		
•	1	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:10
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and "s Ider resist"		

	0	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
-		, , ,	1	14:10
		09/738,667 (("6403460").PN.)	US-P PUB;	14:10
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	-
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	-
		(("6,181,569").PN.)) and ((conducting r		
		conductive) adj (paste or epoxy or resin))		:
-	0	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:11
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((conducting or		
		conductive) near (paste or epoxy or resin))		
-	13	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:11
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM TDB	
		(("6,181,569").PN.)) and (paste or epoxy or	12	
		resin)		
_	7	(((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
-	<b>'</b>	09/738,667 (("6403460").PN.)	US-PGPUB;	14:11
				14.11
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (paste or epoxy or		
		resin)) and (cure or cured or curing)) and		
		(bump or ball or solder)		
-	8	((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:13
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and (paste or epoxy or		
		resin)) and (cure or cured or curing)		
•	11	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:19
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating or	_	
		isolation or dielectric or passivation) adj		
		layer)		
	10	((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
	.5	09/738,667 (("6403460").PN.)	US-PGPUB;	14:19
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
			IBM_TDB	
		(("6,329,288").PN.) (("6,350,668").PN.)	IDM_IDD	
		(("6,181,569").PN.)) and ((insulating r		
		isolati n or dielectric r passivati n) adj		
	<u> </u>	lay r)) and wafer	<u> </u>	<u> </u>

[ <b>.</b>	3	(((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
] -		09/738,667 (("6403460").PN.)	US-P PUB;	14:15
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	14.13
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and electrode		
•	3	((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:15
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
	•	(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and electrode) and		
		(polishing or polish or polished or grind or		
		grinding or grinded)		
_	3	(((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:16
	1	(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	1-1110
		(("6387734").PN.) 10/052,143	DERWENT;	
			1	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and electrode) and		
		(polishing or polish or polished or grind or	,	
		grinding or grinded)) and electroless and		
		(plate or plated or plating)		
-	3	((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:16
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569"). <b>PN.</b> )) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and electrode) and		
		(polishing or polish or polished or grind or		
		grinding or grinded)) and electroless and		
		(plate or plated or plating)) and electrolytic		
_	3	(((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
_		09/738,667 (("6403460").PN.)	US-PGPUB:	14:16
		("5977641").PN.) (("6350633").PN.)	EPO; JPO;	17110
		(("6387784").PN.) (("6350633").PN.)	DERWENT;	
		, , ,	•	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and electrode) and		
		(p lishing or p lish r p lish d r grind r		,
		grinding or grinded)) and I ctroless and		
		(plat r plated r plating)) and I ctr lytic)		
		and (etch retching r tched)		

-	3	(((((((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-P PUB;	14:17
	]	(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating r		
	İ	isolation or dielectric or passivation) adj		
	į	layer)) and wafer) and electrode) and		
		(polishing or polish or polished or grind or		
		grinding or grinded)) and electroless and		
		(plate or plated or plating)) and electrolytic)		
		and (etch or etching or etched)) and (solder		
		or ball or bump)		
	8	(09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:18
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	• • • • • • • • • • • • • • • • • • •
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and electrode		
_	12	((((electrolytic or electrolytically) and	USPAT;	2002/07/19
	"-	electroless and csp) and csp and wafer) and	US-PGPUB:	14:20
		(bump or solder or ball)) and (polish or	EPO; JPO;	14120
		polished or polishing) and (plate or plated or	DERWENT;	
		plating) and electroless and electrolytic	IBM_TDB	
	7		USPAT;	2002/07/19
•	<b>'</b>	(((09/834,629 09794,108 09/794,108		14:20
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:20
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and (polish or polished or		
		polishing) and (plate or plated or plating)		
		and electroless and electrolytic		
-	6	(((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:21
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
	-	(("6,181,569").PN.)) and ((insulating or		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and (polish or polished or		
		polishing) and (plate or plated or plating)		
		and electroless and electrolytic and (etch or		
	1	etched or etching) and (solder or ball or		
		bump) and (sputter or sputtering or		
	1	sputtered)		

-	7	(((09/834,629 09794,108 09/794,108	USPAT;	2002/07/19
		09/738,667 (("6403460").PN.)	US-PGPUB;	14:22
		(("5977641").PN.) (("6350633").PN.)	EPO; JPO;	
		(("6387734").PN.) 10/052,143	DERWENT;	
		(("6,329,288").PN.) (("6,350,668").PN.)	IBM_TDB	
		(("6,181,569").PN.)) and ((insulating r		
		isolation or dielectric or passivation) adj		
		layer)) and wafer) and (polish or polished or		
		polishing) and (plate or plated or plating)	•	
		and electroless and electrolytic and (etch or		
		etched or etching) and (solder or ball or		
		bump)		